SN65C3222E, SN75C3222E 3-V TO 5.5-V MULTICHANNEL RS-232 LINE DRIVERS/RECEIVERS

3-V TO 5.5-V MULTICHANNEL RS-232 LINE DRIVERS/RECEIVERS WITH ±15-kV ESD PROTECTION

TRUMENTS www.ti.com

FEATURES

- ESD Protection for RS-232 Bus Pins

 ±15-kV Human-Body Model (HBM)
 ±8-kV IEC 61000-4-2, Contact Discharge
 - $-\pm$ 15-kV IEC 61000-4-2, Air-Gap Discharge
- Meet or Exceed the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Operate With 3-V to 5.5-V V_{CC} Supply
- Operate up to 1000 kbit/s
- Two Drivers and Two Receivers
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 \times 0.1 μF
- Accepts 5-V Logic Input With 3.3-V Supply

APPLICATIONS

- Battery-Powered Systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

DESCRIPTION/ ORDERING INFORMATION

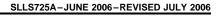
The SN65C3222E and SN75C3222E consist of two line drivers, two line receivers, and a dual charge-pump circuit with \pm 15-kV ESD protection pin to pin (serial-port connection pins, including GND).

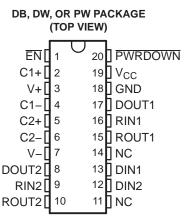
The devices meet the requirements of TIA/EIA-232-F and provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at typical data signaling rates up to 1000 kbit/s and are improved drop-in replacements for industry-popular '3222 two-driver, two-receiver functions.

The SN65C3222E and SN75C3222E can be placed in the power-down mode by setting the power-down (PWRDOWN) input low, which draws only 1 μ A from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V_{CC}, and V- is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting enable (\overline{EN}) high.

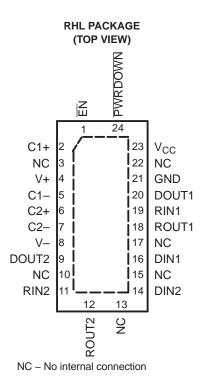


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





NC - No internal connection





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ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	SOIC - DW	Tube of 25	SN75C3222EDW	75C3222E	
	50IC - DVV	Reel of 2000	SN75C3222EDWR	- 7503222E	
0°C to 70°C	SSOP – DB	Tube of 70	SN75C3222EDB	MY222E	
	330P - DB	Reel of 2000	SN75C3222EDBR		
	TSSOP – PW	Tube of 70	SN75C3222EPW	MY222E	
	1330P - PW	Reel of 2000	SN75C3222EPWR		
	SOIC - DW	Tube of 25	SN65C3222EDW	65C3222E	
	3010 - 000	Reel of 2000	SN65C3222EDWR	0003222E	
40°C to 95°C	SSOP – DB	Tube of 70	SN65C3222EDB	MU222E	
–40°C to 85°C	330P - DB	Reel of 2000	SN65C3222EDBR	MU222E	
	TSSOP – PW	Tube of 70	SN65C3222EPW	MU222E	
	1330F - PW	Reel of 2000	SN65C3222EPWR	WIUZZZE	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLES

Each Driver⁽¹⁾

INPUTS		OUTPUT
DIN	PWRDOWN	DOUT
Х	L	Z
L	Н	н
Н	Н	L

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Each Receiver⁽¹⁾

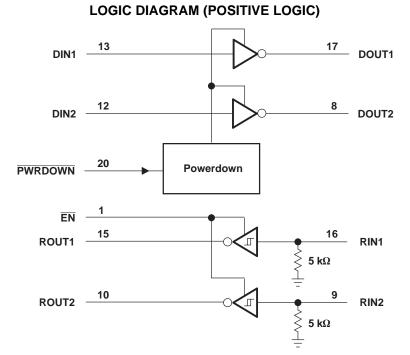
INPU	ITS	OUTPUT
RIN	EN	ROUT
L	L	Н
н	L	L
х	н	Z
Open	L	н

(1) H = high level, L = low level, X = irrelevant,

Z = high impedance (off),

Open = input disconnected or connected driver off

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Pin numbers are for the DB, DW, and PW packages.

Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾		-0.3	6	V
V+	Positive-output supply voltage range ⁽²⁾		-0.3	7	V
V–	Negative-output supply voltage range ⁽²⁾		0.3	-7	V
V+ - V-	Supply voltage difference ⁽²⁾			13	V
V _I Input voltage range	Lange to all the second	Driver (EN, PWRDOWN)	-0.3	6	
	input voltage range	Receiver	-25	25	V
.,		Driver	-13.2	13.2	
Vo	Output voltage range	Receiver	-0.3	V _{CC} + 0.3	V
		DB package		70	
0	Package thermal impedance $^{(3)(4)}$	DW package		58	0000
θ_{JA}		PW package		83	°C/W
		RHL package		TBD	
TJ	Operating virtual junction temperature			150	°C
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltages are with respect to network GND. (2)

Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient (3) temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating a the absolute maximum T_J of 150°C can affect reliability. The package thermal impedance is calculated in accordance with JESD 51-7.

(4)



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Recommended Operating Conditions⁽¹⁾

See Figure 5

				MIN	NOM	MAX	UNIT
	Supply voltage		$V_{CC} = 3.3 V$	3	3.3	3.6	V
	Supply voltage		$V_{CC} = 5 V$	4.5	5	5.5	v
V	Driver and control high-level input voltage	DIN, EN, PWRDOWN	$V_{CC} = 3.3 V$	2			V
V_{H}	Driver and control high-level input voltage Driv, EN,	DIN, EN, FWRDOWN	$V_{CC} = 5 V$	2.4			v
V_{IL}	Driver and control low-level input voltage	DIN, EN, PWRDOWN				0.8	V
VI	Driver and control input voltage DIN, EN, PWRDOWN		0		5.5	V	
VI	V _I Receiver input voltage			-25		25	V
т	Operating free-air temperature			0		70	°C
T _A	Operating nee-an temperature	SN65C3222E	-40		85	C	

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
I _I	Input leakage current (EN, PWRDOWN)			±0.01	±1	μA
	Supply current	No load, $\overline{\text{PWRDOWN}}$ at V_{CC}		0.3	1	mA
ICC	Supply current (powered off)	No load, PWRDOWN at GND		1	10	μA

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

DRIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST COND	ITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	DOUT at $R_L = 3 k\Omega$ to GND,	DIN = GND	5	5.4		V
V _{OL}	Low-level output voltage	DOUT at $R_L = 3 k\Omega$ to GND,	$DIN = V_{CC}$	-5	-5.4		V
I _{IH}	High-level input current	V _I = V _{CC}			±0.01	±1	μA
IIL	Low-level input current	V _I at GND			±0.01	±1	μA
I _{OS}	Short-circuit output current ⁽³⁾	$V_{CC} = 3.6 V$			±35	±60	mA
_	Outraut resistance	$V_{CC} = 5.5 V$	N 10 M	200	4014		
r _o	Output resistance	V_{CC} , V+, and V- = 0 V,	$V_0 = \pm 2 V$	300	10M		Ω
			$V_{CC} = 3 V \text{ to } 3.6 V,$ $V_{O} = \pm 12 V$			±25	۵
I _{OZ}	Output leakage current		$\label{eq:V_CC} \begin{array}{l} V_{CC} = 4.5 \ V \ \text{to} \ 5.5 \ V, \\ V_{O} = \pm 10 \ V \end{array}$			±25	μA

(1)

(2)

Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V. All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one (3) output should be shorted at a time.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER		TEST CONDITIONS		MIN	TYP ⁽²⁾	MAX	UNIT
			C _L = 1000 pF		250			
	Maximum data rate (See Figure 1)	$R_L = 3 k\Omega$, One DOUT switching	C _L = 250 pF,	V_{CC} = 3 V to 4.5 V	1000			kbit/s
	(coorigato I)		C _L = 1000 pF,	V_{CC} = 4.5 V to 5.5 V	1000			
t _{sk(p)}	Pulse skew ⁽³⁾	$C_{L} = 150 \text{ pF} \text{ to } 2500 \text{ pF},$	$R_L = 3 \ k\Omega$ to 7 $k\Omega$,	See Figure 2		300		ns
	Slew rate,	$R_L = 7 k\Omega$,	$C_{L} = 150 \text{ pF} \text{ to } 1000 \text{ pF}$		8		90	
SR(tr)	transition region	region	C _L = 1000 pF		12		60	V/µs
	(see Figure 1)		$C_{L} = 150 \text{ pF} \text{ to } 250 \text{ pF}$		24		150	

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. (3) Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.



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RECEIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	$I_{OH} = -1 \text{ mA}$	V _{CC} – 0.6	V _{CC} – 0.1		V
V _{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V _{IT+}	Desitive going input threshold values	$V_{CC} = 3.3 V$		1.5	2.4	V
	Positive-going input threshold voltage	$V_{CC} = 5 V$		1.8	2.4	V
.,	Negative-going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
V _{IT}		$V_{CC} = 5 V$	0.8	1.5		v
V _{hys}	Input hysteresis (V _{IT+} – V _{IT} –)			0.3		V
I _{OZ}	Output leakage current	<u>EN</u> = 1		±0.05	±10	μA
r _i	Input resistance	$V_{I} = \pm 3 V \text{ to } \pm 25 V$	3	5	7	kΩ

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP ⁽²⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C _L = 150 pF, See Figure 3	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	C _L = 150 pF, See Figure 3	300	ns
t _{en}	Output enable time	C_L = 150 pF, R_L = 3 k Ω , See Figure 4	200	ns
t _{dis}	Output disable time	C_L = 150 pF, R_L = 3 k Ω , See Figure 4	200	ns
t _{sk(p)}	Pulse skew ⁽³⁾	See Figure 3	300	ns

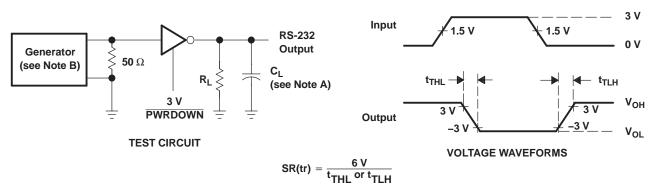
Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V. All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device. (1)

(2)

(3)

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PARAMETER MEASUREMENT INFORMATION



A. C_L includes probe and jig capacitance.

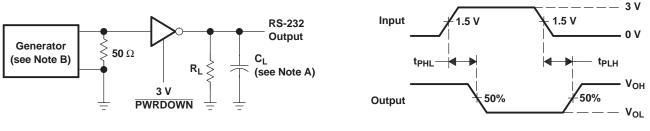
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B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 1. Driver Slew Rate

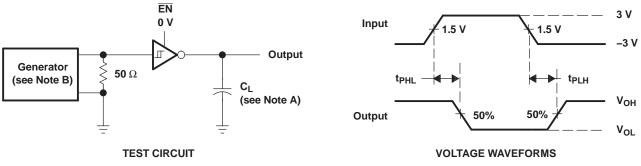


TEST CIRCUIT

VOLTAGE WAVEFORMS

- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω , 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.



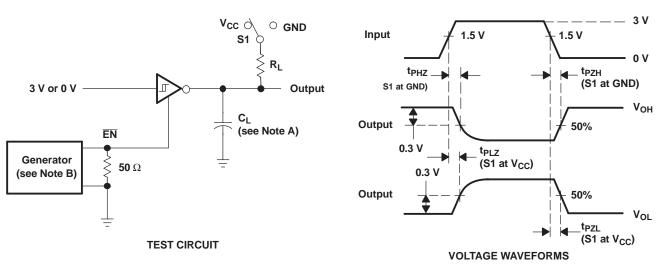


A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z₀ = 50 Ω , 50% duty cycle, t_f ≤ 10 ns, t_f ≤ 10 ns.

Figure 3. Receiver Propagation Delay Times

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PARAMETER MEASUREMENT INFORMATION (continued)

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TEXAS INSTRUMENTS

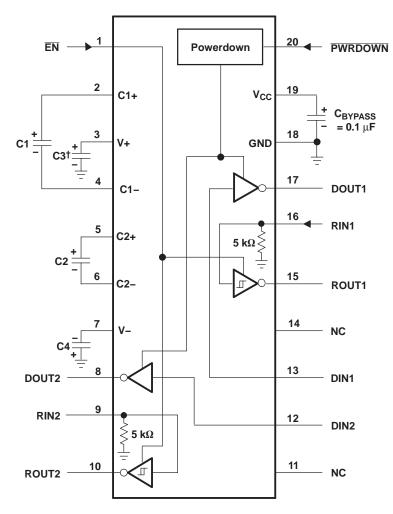
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- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_0 = 50 \ \Omega$, 50% duty cycle, $t_r \le 10 \text{ ns}$, $t_f \le 10 \text{ ns}$.

Figure 4. Receiver Enable and Disable Times

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APPLICATION INFORMATION



 † C3 can be connected to V_CC or GND.

- NOTES: A. Resistor values shown are nominal.
 - B. NC No internal connection
 - C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V _{CC}	C1	C2, C3, and C4
3.3 V \pm 0.3 V	0.1 μ F	0.1 μF
5 V \pm 0.5 V	0.047 μ F	0.33 μF
3 V to 5.5 V	0.1 μF	0.47 μF

V _{CC} vs	CAPACITOR	VALUES
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Figure 5. Typical Operating Circuit and Capacitor Values	Figure 5	Typical	Operating	Circuit and	Capacitor V	/alues
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10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Draining		<u> </u>	(2)	(6)	(3)		(4/5)	
SN65C3222EDB	ACTIVE	SSOP	DB	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EDBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EDW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E	Samples
SN65C3222EDWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E	Samples
SN65C3222EPW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EPWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EPWRG4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN75C3222EPW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY222E	Samples
SN75C3222EPWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY222E	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



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PACKAGE OPTION ADDENDUM

10-Dec-2020

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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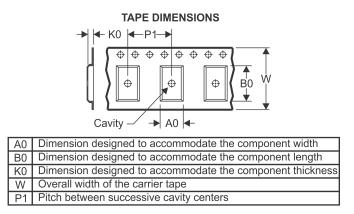
PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



All dimensions are nominal Device	1	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3222EDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3222EDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN65C3222EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN75C3222EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

30-Dec-2020



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3222EDBR	SSOP	DB	20	2000	853.0	449.0	35.0
SN65C3222EDWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN65C3222EPWR	TSSOP	PW	20	2000	853.0	449.0	35.0
SN75C3222EPWR	TSSOP	PW	20	2000	853.0	449.0	35.0

PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994. β . This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153



LAND PATTERN DATA



NOTES: Α. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
 C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



DW0020A

EXAMPLE BOARD LAYOUT

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DW0020A

EXAMPLE STENCIL DESIGN

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DB0020A



PACKAGE OUTLINE

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



DB0020A

EXAMPLE BOARD LAYOUT

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DB0020A

EXAMPLE STENCIL DESIGN

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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